

1. (Amended) A method of forming a mask, comprising:

forming a first layer of material over a substrate;

forming an opaque layer overlying said first layer of material, said opaque layer having at least one opening therein filled with a first resist material, said first resist material residing over said first layer of material and defining areas of said first layer of material which are to be removed;

using said first resist material as a mask to remove said areas of said first layer of material; and

removing said first resist material.

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2. (Amended) The method of claim 1, wherein the using of said first resist material as a mask comprises providing a first region from which said first layer of material is removed, and the removing of said first resist material comprises providing a second region from which said first resist material is removed, said first and second regions having different phase shift characteristics with respect to light transmitted therethrough.

8. (Amended) The method of claim 1, wherein the forming of said opaque layer comprises:

depositing a second resist material on said opaque layer;

removing a portion of said second resist material, leaving said opening;

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etching an uncovered portion of said opaque layer underlying the removed portion of said second resist material, thereby deepening said opening; and
removing the remainder of said second resist material.

9. (Amended) The method of claim 8, wherein the using of said first resist as a mask comprises:

providing said first resist material within said opening and over said opaque layer;

directing a first exposure through said substrate to expose a portion of said first resist material;

hardening the exposed portion of said first resist material;

directing a second exposure at said first resist material to remove any unhardened portions of said first resist material;

providing a second material over said opaque layer and said hardened portion of said first resist material;

performing a lithographic step on a portion of said second material overlying and bounded by said first resist material to expose and remove said portion of said second material; and

etching said first layer of material underlying said exposed and removed portion of said second material.

10. (Amended) The method of claim 9, wherein said first resist material is a positive-tone resist material capable of making an image reverse tone.

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cont.

11. (Amended) The method of claim 9, wherein the exposed portion of said first resist material is hardened by baking.

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Cancel claims 37-40, 42 and 43.